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Letter to the Editor

Radiative transition quantum efficiency of ${}^{2}H_{11/2}$ and ${}^{4}S_{3/2}$ states of trivalent erbium ion in oxyfluoride tellurite glass

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Abstract

The optical transition intensity parameters of erbium ion in oxyfluoride tellurite glass were derived by fitting the absorption spectrum according to Judd–Ofelt theory. With the obtained parameters the radiative transition rates, branching ratios and lifetimes of different states in Er^{3+} doped oxyfluoride tellurite glass were calculated. Temperature dependences of the emission spectrum and the lifetime of ${}^2H_{11/2}$, ${}^4S_{3/2}$ were measured within the temperature range from 108 to 315 K. The method for calculating the radiative transition quantum efficiency of the ${}^2H_{11/2}$ and ${}^4S_{3/2}$ states, which are in thermal equilibrium, was discussed. The quantum efficiencies of the ${}^2H_{11/2}$ and ${}^4S_{3/2}$ states of Er^{3+} in oxyfluoride tellurite glass were calculated. © 2004 Elsevier B.V. All rights reserved.

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1. Introduction

Since up-conversion fluorescence in a tellurite matrix was observed for the first time in $\rm Er_2O_3$ doped $70 \rm TeO_2-30 \rm Na_2O$ glass at room temperature [1], the up-converted green emission corresponding to $^2H_{11/2},~^4S_{3/2} \rightarrow ^4I_{15/2}$ transition of the trivalent erbium ion has been extensively investigated [2,3]. The energy gap between $^2H_{11/2}$ and $^4S_{3/2}$ is about some hundreds wavenumbers, which is in the range of phonon energy. Thus, as it is well known, the $^4S_{3/2}$ and $^2H_{11/2}$ levels are always in thermal equilibrium [4]; the relative intensity of the $^4S_{3/2}$ and $^2H_{11/2}$ emissions is temperature dependent. However, little attention has been paid to the radiative transition quantum efficiency of the $^2H_{11/2},~^4S_{3/2}$ states.

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In our work, we have investigated the temperature dependence of the radiative transition quantum efficiencies of the ${}^2H_{11/2}$, ${}^4S_{3/2}$ states. Absorption spectrum of the sample at room temperature has been measured and analyzed using the Judd–Ofelt theory. Emission spectra and decay curves of ${}^2H_{11/2}$, ${}^4S_{3/2}$ states have been measured at different temperatures ranged from 108 to 329 K. Based on these experiments, the method for evaluating the quantum efficiency of the ${}^2H_{11/2}$ and ${}^4S_{3/2}$ states has been discussed.

2. Experiment

The tellurite glass sample used in our measurement is with a mol% composition of 70TeO₂–9PbF₂–10AlF₃–10BaF₂–1Er₂O₃. The raw materials of the fluoride and telluride are of analytic purity, the erbium oxide is of spectroscopic purity. Accurately weighed 10g batches are fully mixed and moved into an alumina crucible.

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Then, put them into a muffle stove when the temperature of the stove rises to 800 °C and keep this temperature for 15 min. The melts are cast into a stainless steel plate and annealed at 100 °C. Samples for the optical property measurement are cut and polished to the thickness of 2 mm.

Optical absorption spectrum in the ultraviolet, visible and near infrared regions is measured by a spectrophotometer (Perkin-Elmer Lambda 9 UV/VIS /NIS/ NIR) at room temperature. The refractive indices of the sample are obtained by a variable angle incidence spectroscopic ellipsometer (M-2000 J.A.Woollam Co, Inc. USA). In the measurement of the emission spectra, the sample is excited by 355 nm, the third harmonic from a QuantaRay DCR2A YAG:Nd pulsed laser. The emission is dispersed by a computer-controlled double-grating monochromator (SPEX-1403) and detected by a photomultiplier tube (Hamamatsu R945). The signal from the detector passes through a PARC 162 boxcar and is processed by a computer. The fluorescence decay curves are measured by a digital oscilloscope (Tektronix TDS3052 500 MHz). The sample is mounted in a cryostat for temperature-dependent studies.

3. Results

3.1. Judd–Ofelt parameters, radiative transition lifetime and branching ratios

Fig. 1 shows the absorption spectrum of erbium ion in 70TeO_2 – 9PbF_2 – 10AlF_3 – 10BaF_2 – $1\text{Er}_2\text{O}_3$ glass at room temperature. Ten peaks in the absorption spectrum correspond to the ${}^4\text{I}_{15/2} \rightarrow {}^2\text{H}_{9/2}, \, {}^4\text{F}_{3/2}, \, {}^4\text{F}_{5/2}, \, {}^4\text{F}_{7/2}, \, {}^2\text{H}_{11/2},$

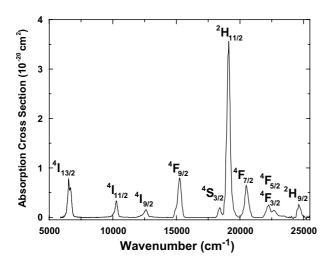


Fig. 1. Absorption spectrum of Er^{3+} doped oxyfluoride tellurite glass of molar composition $70 TeO_2 - 9PbF_2 - 10AlF_3 - 10BaF_2 - 1Er_2O_3.$

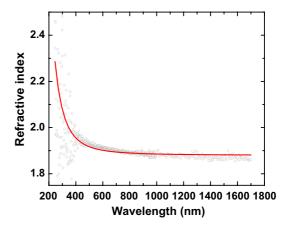


Fig. 2. The dependence of the refractive index on the wavelength of incident light.

 4 S_{3/2}, 4 F_{9/2}, 4 I_{9/2}, 4 I_{11/2}, 4 I_{13/2} absorption transitions, respectively. Fig. 2 is the dependence of the refractive index on the wavelength of the incident light. With these experimental data and Judd–Ofelt theory [5,6], we obtained the intensity parameters as $\Omega_2 = 6.74 \times 10^{-20}$, $\Omega_4 = 1.88 \times 10^{-20}$ and $\Omega_6 = 1.54 \times 10^{-20}$ cm², with rms deviation $\delta = 23 \times 10^{-22}$ cm². With the Ωs, we calculate the radiative transition rates, lifetimes and branching ratios of various energy levels. The results are shown in Table 1.

3.2. Temperature dependence of green emission of the $^2H_{11/2},\,^4S_{3/2}$ state

Fig. 3 shows the emission spectra of the ${}^2H_{11/2}$, ${}^4S_{3/2} \rightarrow {}^4I_{15/2}$ transitions at 99 K and 288 K, respectively. At 99 K, the emission from 18 600 to 19 500 wavenumbers corresponding to ${}^2H_{11/2} \rightarrow {}^4I_{15/2}$ is hardly observed. With the temperature increasing, the fluorescence intensity of the ${}^2H_{11/2} \rightarrow {}^4I_{15/2}$ transition is enhanced gradually. At 288 K, it can be observed clearly. ${}^2H_{11/2}$ and ${}^4S_{3/2}$ states, in thermal equilibrium, decay with the same rate [7–11]. Because they have different radiative transition rates, the decay rate will change with temperature. The lifetime of the fluorescence can be expressed as [7–11]

$$\tau(T) = \frac{1}{W_0 + W_1 e^{-\Delta E/kT}},\tag{1}$$

where W_0 is the transition rate of the $^4S_{3/2}$ state, including radiative and non-radiative transitions, W_1 denotes the transition rate of the $^2H_{11/2}$ state, ΔE is the energy gap between two energy levels [7–11].

Fig. 4 shows the fluorescence decay curves monitored at 552 nm at different temperatures. Fitting the experimental curves with an exponential decay function, we obtained the luminescence decay lifetimes of the ${}^{2}H_{11/2}$, ${}^{4}S_{3/2}$

Table 1 The oscillator strengths, transition probabilities, branch ratios and lifetimes of the Er^{3+} states in oxyfluoride tellurite glass

Initial state	Final state	Wave-number	Oscillator strength (10 ⁻⁸)		Transition rate (S ⁻¹)		Branch ratio (%)	Lifetime (ms)
			ED	MD*	ED	MD*		
² H _{11/2}	⁴ S _{3/2}	754	4.72		0.06		0	0.06
	$^{4}F_{9/2}$	3882	160.76		57.09		0.34	
	$^{4}I_{9/2}$	6740	202.58		217.25		1.29	
	${}^{4}I_{11/2} \\ {}^{4}I_{13/2}$	8991	80.08		153.18		0.91	
	$^{4}I_{13/2}$	12625	71.88		272.79		1.63	
	$^{4}I_{15/2}$	19120	1798.54		16025.36		95.81	
⁴ S _{3/2}	$^{4}F_{9/2}$	3128	5.38		1.24		0.03	0.62
	$^{4}I_{9/2}$	5986	157		132.73		3.47	
	⁴ I _{9/2} ⁴ I _{11/2}	8237	51.36		82.39		2.15	
	$^{4}I_{13/2}$	11871	306.88		1027.95		26.92	
	${}^{4}I_{13/2}$ ${}^{4}I_{15/2}$	18366	314.17		2573.07		67.4	
$^{4}F_{9/2}$	$^{4}I_{9/2}$	2858	47.27		9.09		0.29	0.32
	$^{4}I_{11/2}$	5109	84.56		52.05		1.67	
	$^{4}I_{13/2}$	8743	82.68		149.5		4.79	
	$^{4}I_{15/2}$	15238	521.94		2905.93		93.24	
$^{4}I_{9/2}$	$^{4}I_{11/2}$	2251	16.49	32.68	1.96	3.90	1.50	2.63
	$^{4}I_{13/2}$	5885	127.71		104.35		27.44	
	$^{4}I_{15/2}$	12380	74.21		270.66		71.06	
$^{4}I_{11/2}$	$^{4}I_{13/2}$	3634	130.91	58.48	40.73	18.20	15.65	2.66
	$^{4}I_{15/2}$	10129	130.59		317.52		84.35	
$^{4}I_{13/2}$	$^{4}I_{15/2}$	6493	202.27	67.80	201.30	67.46	100.00	3.72

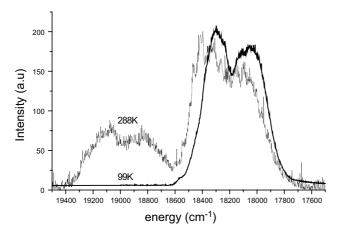


Fig. 3. The emission spectra of $^2H_{11/2},\,^4S_{3/2}\rightarrow\,^4I_{15/2}$ at 99 K and 288 K, respectively.

states. The dependence of the lifetime on the temperature is shown in Fig. 5 together with the fitting curve according to Eq. (1). The fitting parameters are $W_0 = 666.8 \, \mathrm{s}^{-1}$, $W_1 = 2.89 \times 10^4 \, \mathrm{s}^{-1}$, $\Delta E = 611 \, \mathrm{cm}^{-1}$. From these parameters, the lifetime of the $^4\mathrm{S}_{3/2}$ state at low temperature is $1/W_0 = 1.50 \, \mathrm{ms}$, and the transition rate of the $^2\mathrm{H}_{11/2}$ state is about 40 times larger than that of the $^4\mathrm{S}_{3/2}$ state.

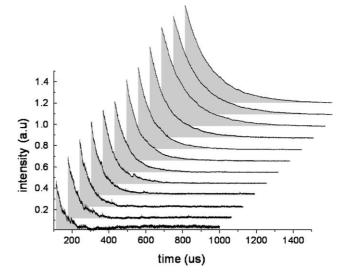


Fig. 4. The decay curves of $552\,\mathrm{nm}$ at different temperature, the temperatures from inside to outside is $108\,\mathrm{K}$, $118\,\mathrm{K}$, $127\,\mathrm{K}$, $179\,\mathrm{K}$, $205\,\mathrm{K}$, $219\,\mathrm{K}$, $235\,\mathrm{K}$, $248\,\mathrm{K}$, $262\,\mathrm{K}$, $275\,\mathrm{K}$, $287\,\mathrm{K}$, $301\,\mathrm{K}$, the data of the lifetimes are listed in Table 2.

4. Discussions

Quantum efficiency η is an important parameter for a luminescence material. It can be expressed as

(2)

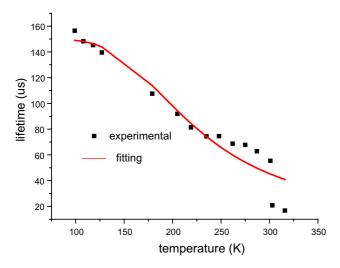


Fig. 5. Relationship between fluorescence lifetime and temperature.

 $^4S_{3/2}$ states, the numbers of electrons depopulated through the $^2H_{11/2}$ state is

$$Ne^{-\Delta E/kT} \int_0^\infty W_1 \exp[-(W_0 + e^{-\Delta E/kT}W_1)t]dt$$
$$= \frac{NW_1 e^{-\Delta E/kT}}{W_0 + e^{-\Delta E/kT}W_1},$$

while that through the radiative transition of the ${}^{2}H_{11/2}$ state is

$$\frac{NA_{\rm r1}e^{-\Delta E/kT}}{W_0 + e^{-\Delta E/kT}W_1},$$

where $A_{\rm r1}$ denotes the radiative transition rate of the $^2{\rm H}_{11/2}$ state. So, the radiative transition quantum efficiency of the $^2{\rm H}_{11/2}$ state can be expressed as $A_{\rm r1}/W_{\rm l}$. By analogy, the radiative transition quantum efficiency of the $^4{\rm S}_{3/2}$ state can be expressed as $A_{\rm r0}/W_0$, where $A_{\rm r0}$ is the radiative transition rate of the $^4{\rm S}_{3/2}$ state. That

$$\eta = \frac{\text{Number of photons generated in the radiative transition}}{\text{Number of electrons excited to the excited state}}.$$

In rare-earth luminescence materials, η is always depicted as

$$\eta = \frac{\tau_{\exp}(T)}{\tau_{\text{cal}}(T)},\tag{3}$$

where $\tau_{\rm exp}$ and $\tau_{\rm cal}$ denote the experimental lifetime and the radiative transition lifetime calculated by the Judd–Ofelt theory. However, it is invalid in our case where the $^2H_{11/2}$ and $^4S_{3/2}$ states are in thermal equilibrium, since the measured decay time is not caused merely by an individual state [7–11]. Among N electrons on the $^2H_{11/2}$ and

is, in evaluating the quantum efficiencies of ${}^4S_{3/2}$ and ${}^2H_{11/2}$, instead of the experimental $\tau_{\rm exp}$, we should use $1/W_0$ and $1/W_1$ obtained from the fitting.

System having small energy gap like the ${}^2H_{11/2}$ and ${}^4S_{3/2}$ states also can be treated as a whole to calculate their radiative transition quantum efficiency. Among these N electrons on the ${}^2H_{11/2}$ and ${}^4S_{3/2}$ states, the number of electrons depopulated via radiative transition is

$$\frac{N(A_0 + A_1 e^{-\Delta E/kT})}{W_0 + e^{-\Delta E/kT}W_1}.$$

Table 2 The calculated radiative transition rates, measured lifetimes, and the quantum efficiencies of the ${}^4S_{3/2}$, ${}^2H_{11/2}$ states at different temperatures

Temperature (K)	$A_{\rm r0} + A_{r1} {\rm e}^{-\Delta E/kT} ({\rm s}^{-1})$	τ _{exp} (μs)	Quantum efficiency (%)
99	3820	156.49	56.8
108	3822	148.24	56.6
118	3827	145.26	55.6
127	3834	139.52	53.5
179	3940	107.48	42.3
205	4046	91.88	37.2
219	4118	81.34	33.5
235	4213	74.38	31.3
248	4299	74.55	32.1
262	4399	68.69	30.2
275	4499	67.76	30.5
287	4597	62.79	28.9
301	4716	55.34	26.1
303	4734	20.77	9.8
316	4850	16.68	8.1
329	4933	19.87	9.8

So the radiative transition quantum efficiency can be written as

$$\eta(T) = \frac{A_{\rm r0} + A_{\rm r1} e^{-\Delta E/kT}}{W_0 + W_1 e^{-\Delta E/kT}} = \tau_{\rm exp} (A_{\rm r0} + A_{\rm r1} e^{-\Delta E/kT}). \tag{4}$$

With Eq. (4), the quantum efficiencies of the sample at different temperature can be obtained. The results are showed in Table 2.

5. Conclusions

The optical transition intensity parameters of erbium ion in oxyfluoride tellurite glass are obtained by fitting the absorption spectrum with Judd–Ofelt theory. The intensity parameters are $\Omega_2 = 6.74 \times 10^{-20} \, \mathrm{cm}^2$, $\Omega_4 = 1.88 \times 10^{-20} \, \mathrm{cm}^2$ and $\Omega_6 = 1.54 \times 10^{-20} \, \mathrm{cm}^2$. With the obtained parameters, the radiative transition rates, branching ratios and lifetimes of different states in Er³⁺ doped oxyfluoride tellurite glass are calculated. Emission spectra and fluorescence decay curves at different temperature are measured. With the method discussed, we calculate the radiative quantum efficiency of the $^2H_{11/2}$, $^4S_{3/2}$ states of erbium ion at different temperature.

Acknowledgments

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